

## P-Channel 20-V (D-S) MOSFET

PRODUCT SUMMARY		
$V_{DS}$ (V)	$R_{DS(on)}$ ( $\Omega$ )	$I_D$ (A)
- 20	0.00875 at $V_{GS} = - 4.5$ V	- 14
	0.01075 at $V_{GS} = - 2.5$ V	- 12
	0.0135 at $V_{GS} = - 1.8$ V	- 11

### FEATURES

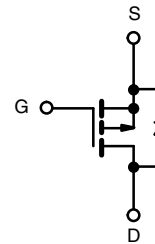
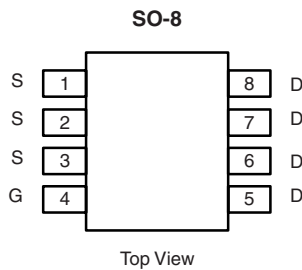
- Halogen-free Option Available
- TrenchFET<sup>®</sup> Power MOSFET



**RoHS**  
COMPLIANT

### APPLICATIONS

- Game Station
- Load Switch



P-Channel MOSFET

Ordering Information: Si4421DY-T1-E3 (Lead (Pb)-free)  
Si4421DY-T1-GE3 (Lead (Pb)-free and Halogen-free)

ABSOLUTE MAXIMUM RATINGS $T_A = 25$ °C, unless otherwise noted					
Parameter	Symbol	10 s	Steady State	Unit	
Drain-Source Voltage	$V_{DS}$	- 20		V	
Gate-Source Voltage	$V_{GS}$	$\pm 8$			
Continuous Drain Current ( $T_J = 150$ °C) <sup>a</sup>	$I_D$	$T_A = 25$ °C	- 14	- 10	A
		$T_A = 70$ °C	- 11.5	- 8	
Pulsed Drain Current	$I_{DM}$	- 40			
Continuous Source Current (Diode Conduction) <sup>a</sup>	$I_S$	- 2.7	- 1.36		
Maximum Power Dissipation <sup>a</sup>	$P_D$	$T_A = 25$ °C	3.0	1.5	W
		$T_A = 70$ °C	1.9	0.95	
Operating Junction and Storage Temperature Range	$T_J, T_{stg}$	- 55 to 150		°C	

THERMAL RESISTANCE RATINGS					
Parameter	Symbol	Typical	Maximum	Unit	
Maximum Junction-to-Ambient <sup>a</sup>	$R_{thJA}$	$t \leq 10$ s	33	42	°C/W
		Steady State	70	85	
Maximum Junction-to-Foot (Drain)	$R_{thJF}$	16	21		

Notes:

a. Surface Mounted on 1" x 1" FR4 board.

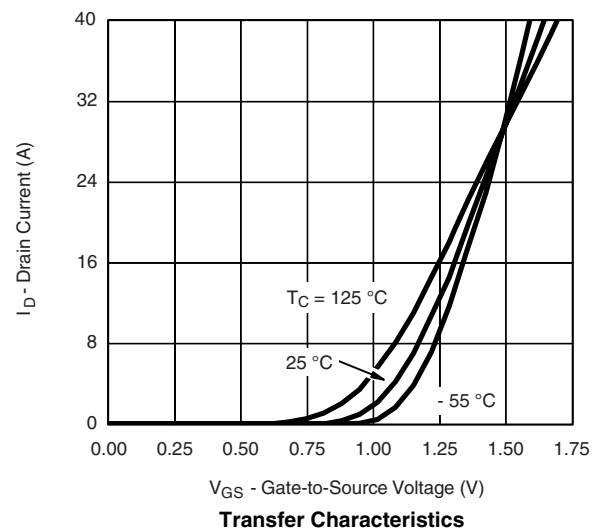
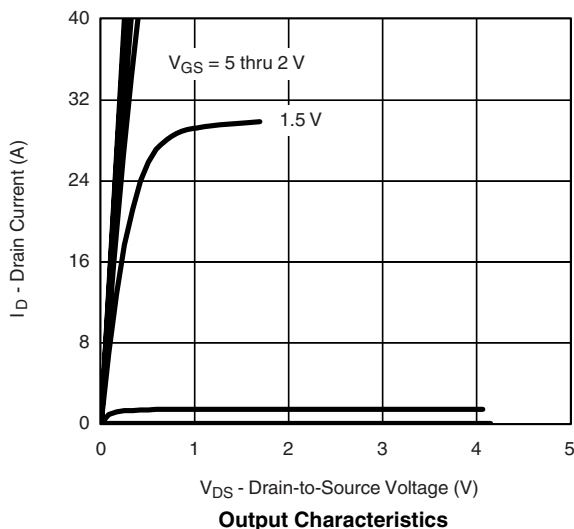
<b>SPECIFICATIONS</b> $T_J = 25\text{ }^\circ\text{C}$ , unless otherwise noted						
Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
<b>Static</b>						
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = -850\text{ }\mu\text{A}$	-0.4		-0.8	V
Gate-Body Leakage	$I_{GSS}$	$V_{DS} = 0\text{ V}, V_{GS} = \pm 8\text{ V}$			$\pm 100$	nA
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS} = -20\text{ V}, V_{GS} = 0\text{ V}$			-1	$\mu\text{A}$
		$V_{DS} = -20\text{ V}, V_{GS} = 0\text{ V}, T_J = 70\text{ }^\circ\text{C}$			-10	
On-State Drain Current <sup>a</sup>	$I_{D(on)}$	$V_{DS} = -5\text{ V}, V_{GS} = -4.5\text{ V}$	-30			A
Drain-Source On-State Resistance <sup>a</sup>	$R_{DS(on)}$	$V_{GS} = -4.5\text{ V}, I_D = -14\text{ A}$		0.007	0.00875	$\Omega$
		$V_{GS} = -2.5\text{ V}, I_D = -12\text{ A}$		0.0085	0.01075	
		$V_{GS} = -1.8\text{ V}, I_D = -11\text{ A}$		0.011	0.0135	
Forward Transconductance <sup>a</sup>	$g_{fs}$	$V_{DS} = -10\text{ V}, I_D = -14\text{ A}$		55		S
Diode Forward Voltage <sup>a</sup>	$V_{SD}$	$I_S = -2.7\text{ A}, V_{GS} = 0\text{ V}$		-0.6	-1.1	V
<b>Dynamic<sup>b</sup></b>						
Total Gate Charge	$Q_g$	$V_{DS} = -10\text{ V}, V_{GS} = -4.5\text{ V}, I_D = -14\text{ A}$		82	125	nC
Gate-Source Charge	$Q_{gs}$		10			
Gate-Drain Charge	$Q_{gd}$		27			
Gate Resistance	$R_g$			3		$\Omega$
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = -10\text{ V}, R_L = 10\text{ }\Omega$ $I_D \cong -1\text{ A}, V_{GEN} = -4.5\text{ V}, R_G = 6\text{ }\Omega$		45	70	ns
Rise Time	$t_r$		90	140		
Turn-Off Delay Time	$t_{d(off)}$		350	550		
Fall Time	$t_f$		170	260		
Source-Drain Reverse Recovery Time	$t_{rr}$		$I_F = -2.1\text{ A}, di/dt = 100\text{ A}/\mu\text{s}$		135	

Notes:

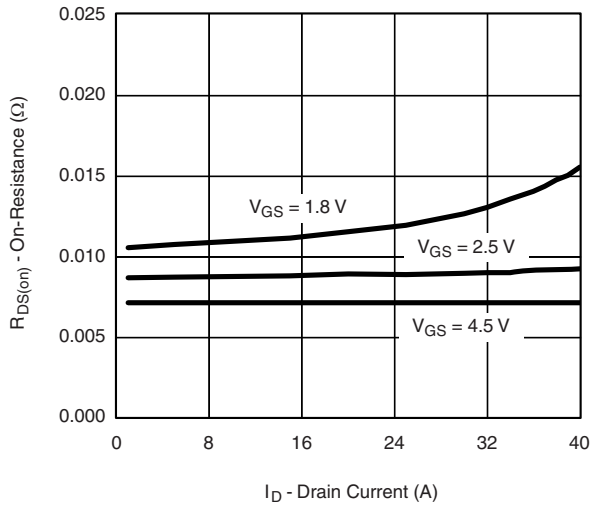
- a. Pulse test; pulse width  $\leq 300\text{ }\mu\text{s}$ , duty cycle  $\leq 2\%$ .
- b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

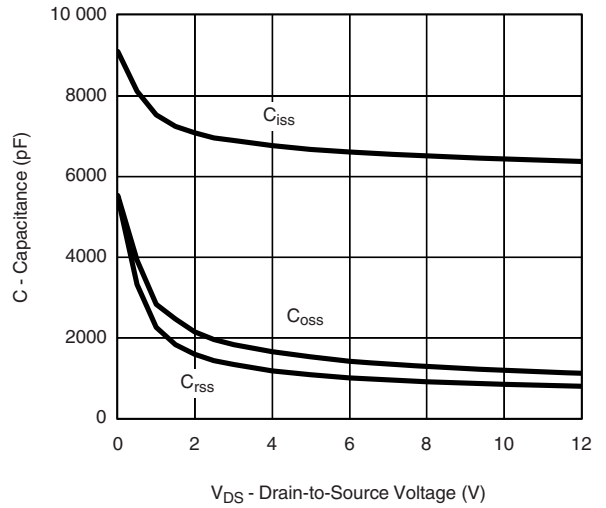
**TYPICAL CHARACTERISTICS**  $25\text{ }^\circ\text{C}$ , unless otherwise noted



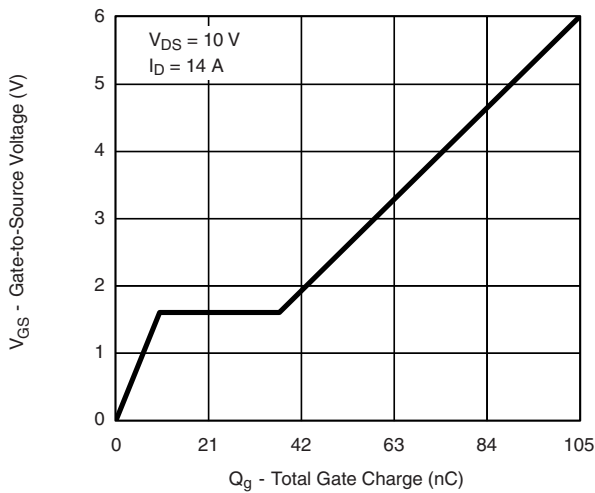
**TYPICAL CHARACTERISTICS** 25 °C, unless otherwise noted



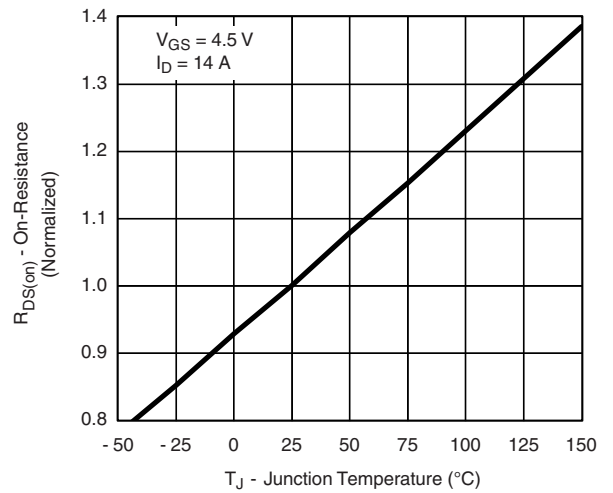
**On-Resistance vs. Drain Current**



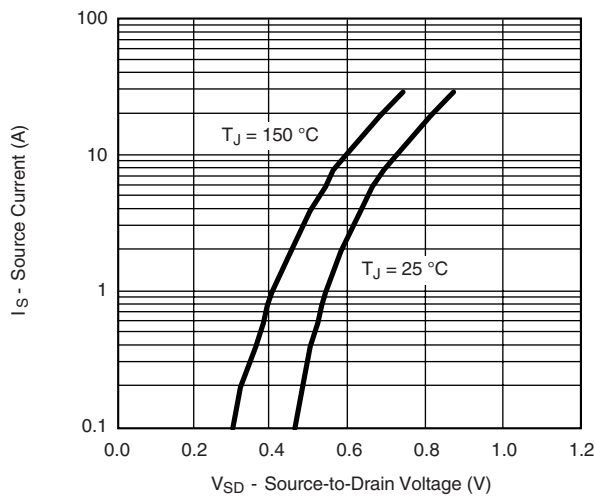
**Capacitance**



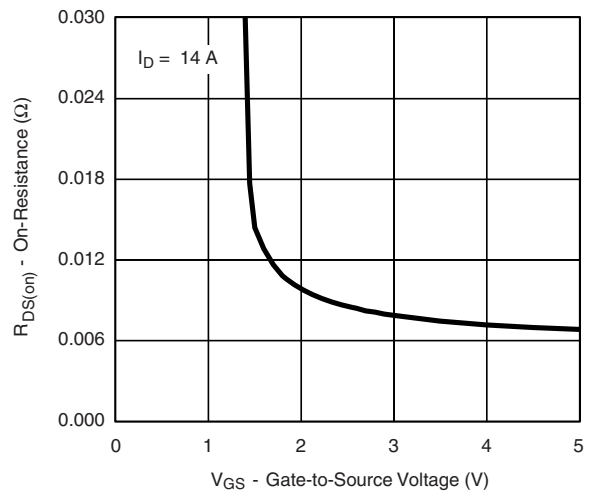
**Gate Charge**



**On-Resistance vs. Junction Temperature**

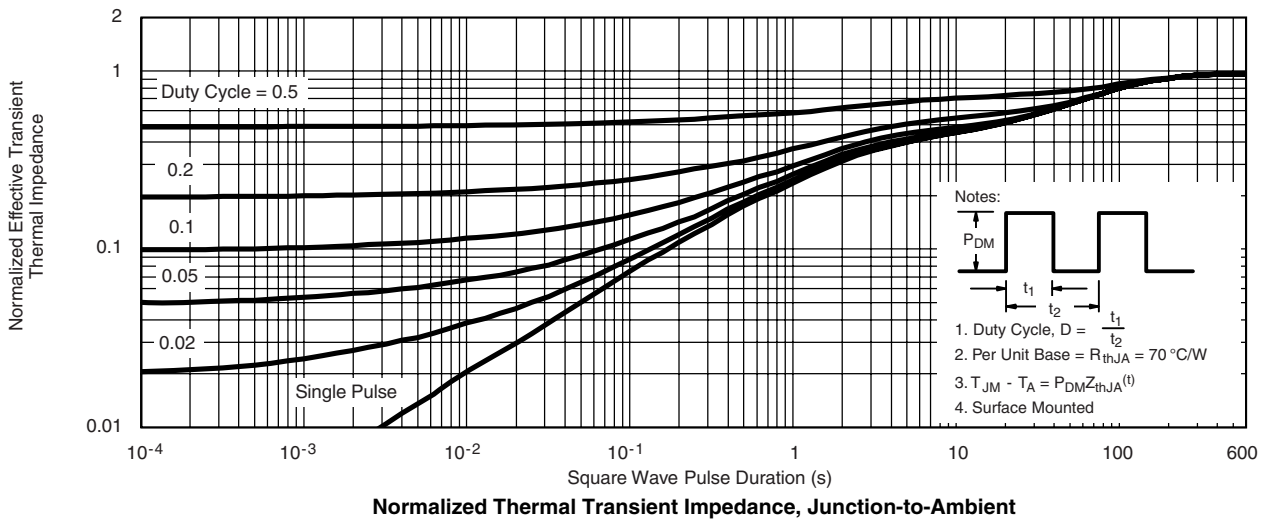
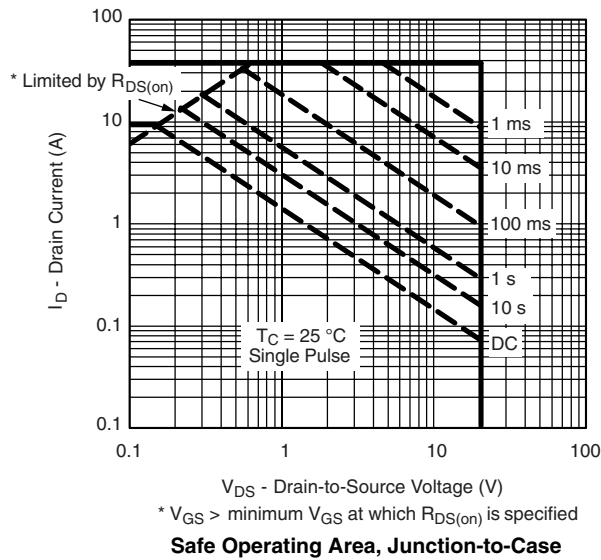
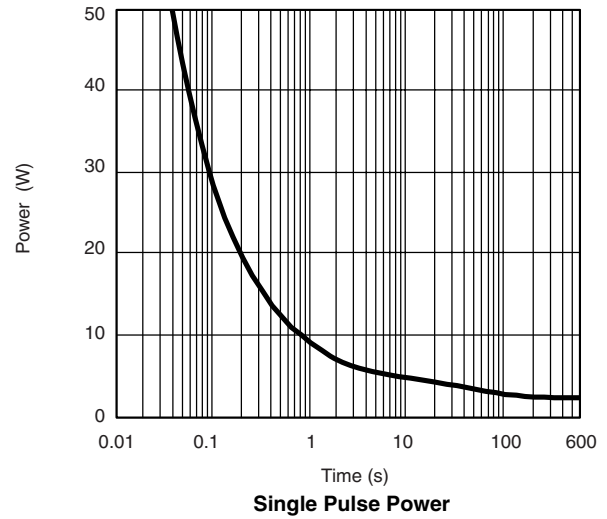
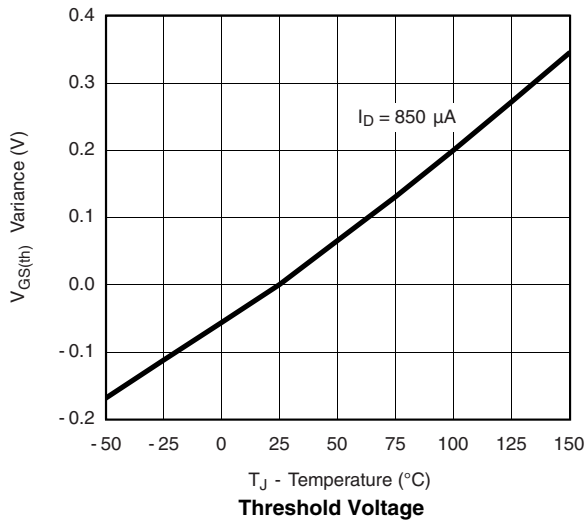


**Source-Drain Diode Forward Voltage**



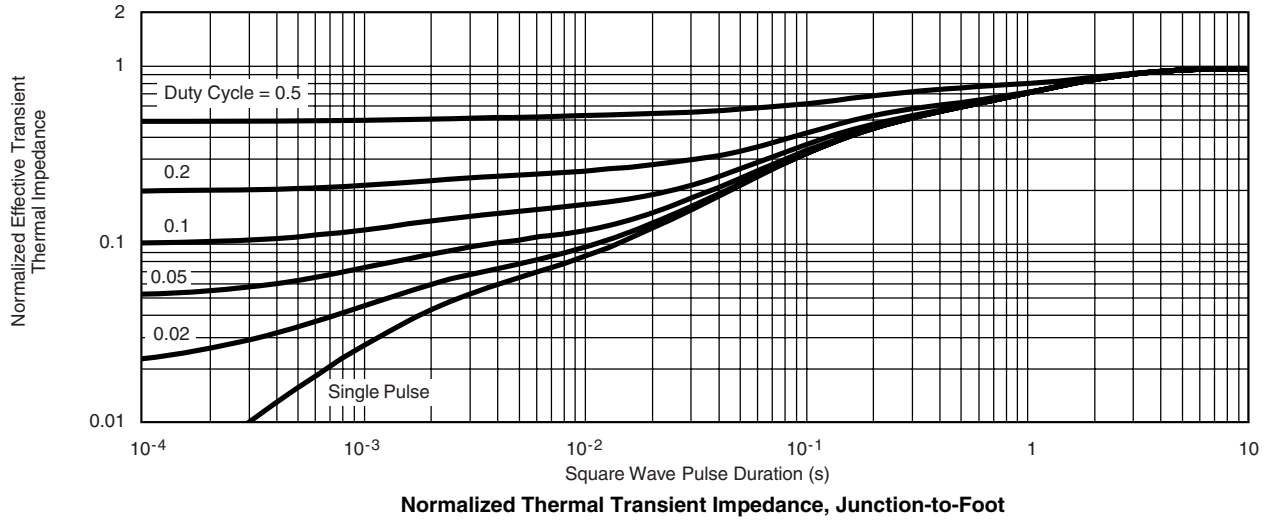
**On-Resistance vs. Gate-to-Source Voltage**

**TYPICAL CHARACTERISTICS** 25 °C, unless otherwise noted





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